A METHOD OF FABRICATING A THIN FILM

ABSTRACT OF THE DISCLOSURE

A method of fabricating a thin film comprises:

a) a step for implantation by bombarding one face of a substrate formed from a semiconductor material with ions to form, at a predetermined depth in the substrate, a concentrated layer of said implanted ions, said concentrated layer defining a thin film in the upper portion of the substrate;

b) a step for bringing the face of the substrate into intimate contact with a stiffener;

c) a step for detaching the thin film in contact with the stiffener by splitting at the concentrated layer of ions.

The method further comprises, after implantation step a) and before detachment step c), a heat treatment step to trap contaminants, which step does not cause splitting of the substrate at the concentrated layer of implanted ions, and after step c), a step of withdrawing the zone perturbed by trapping the contaminants and by detachment step c).

FIG. 2